

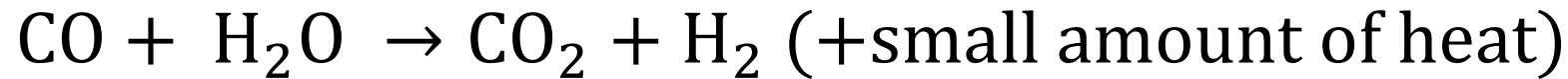


Room Temperature Electrochemical Synthesis of Nanostructured Cu_2O Thin Films

Presented By: Akhilender Jeet Singh
IIT Bombay, India

Ways to produce Hydrogen

1. Steam Methane Reforming



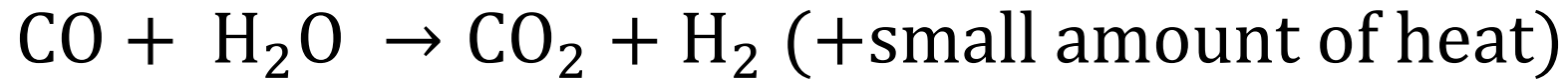
2. Electrocatalytic Water Splitting



3. Photo-electrochemical Water Splitting

Ways to produce Hydrogen

1. Steam Methane Reforming

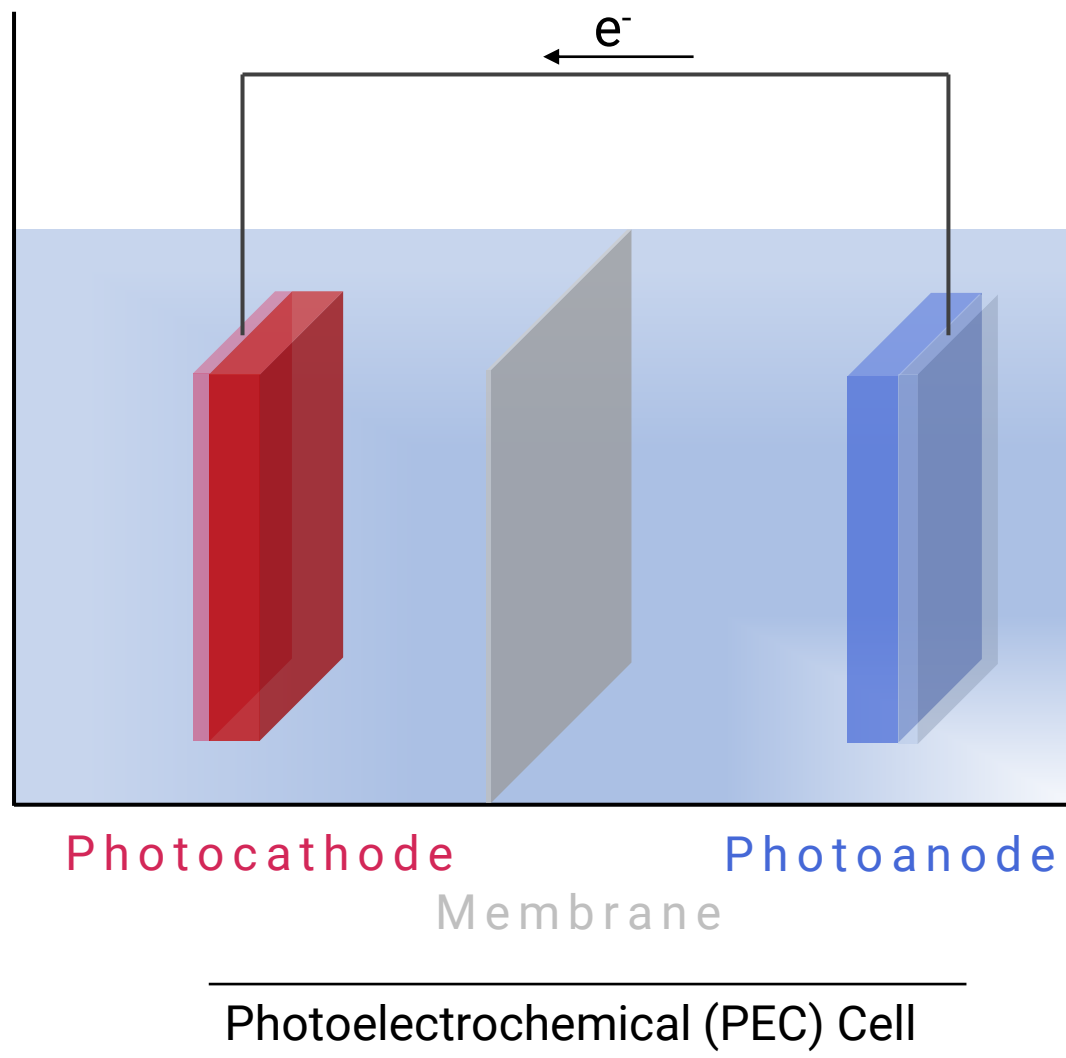


2. Electrocatalytic Water Splitting



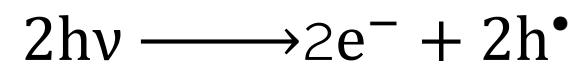
3. Photo-electrochemical Water Splitting

Photoelectrochemical Water Splitting

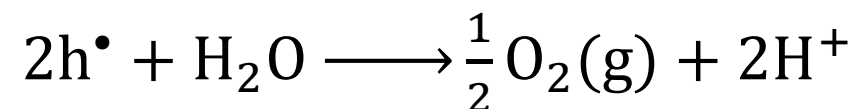


$$\Delta G^0 = +237.14 \text{ kJ/mol}$$

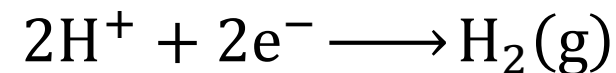
$$E_i = h\nu = 1.23 \text{ eV}$$



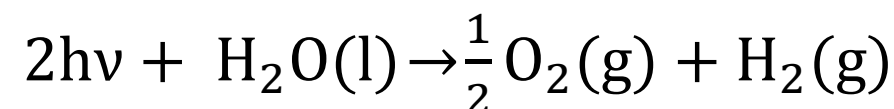
Photoanode: Water Oxidation



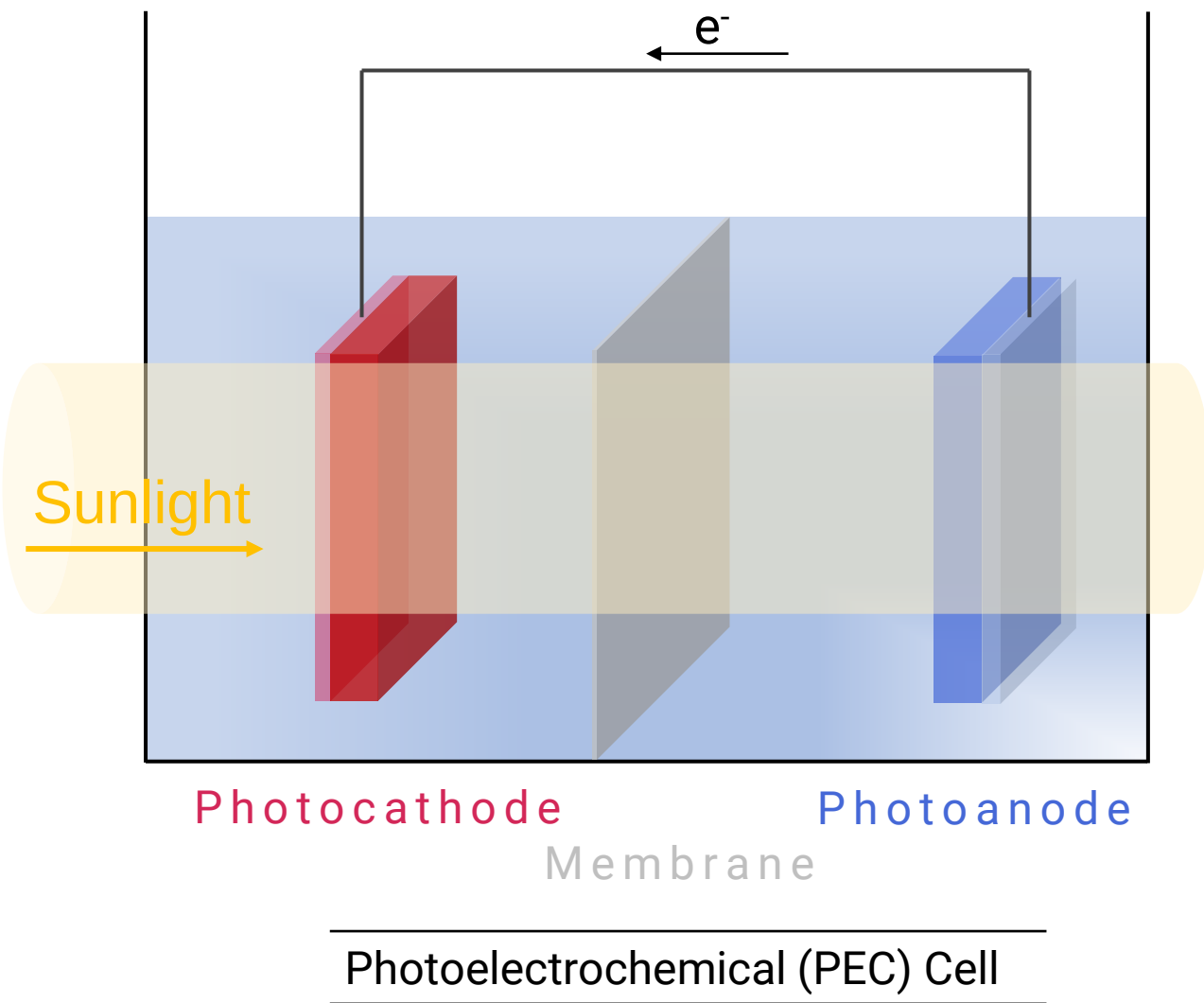
Photocathode: Water Reduction



Overall reaction:

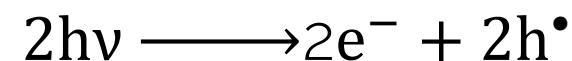


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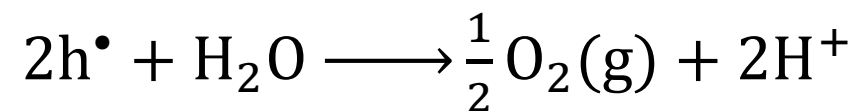


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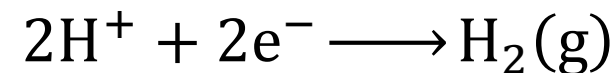
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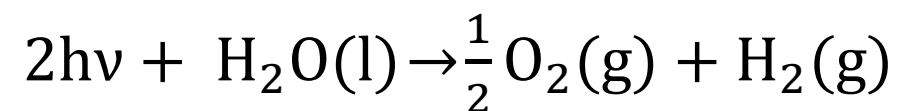
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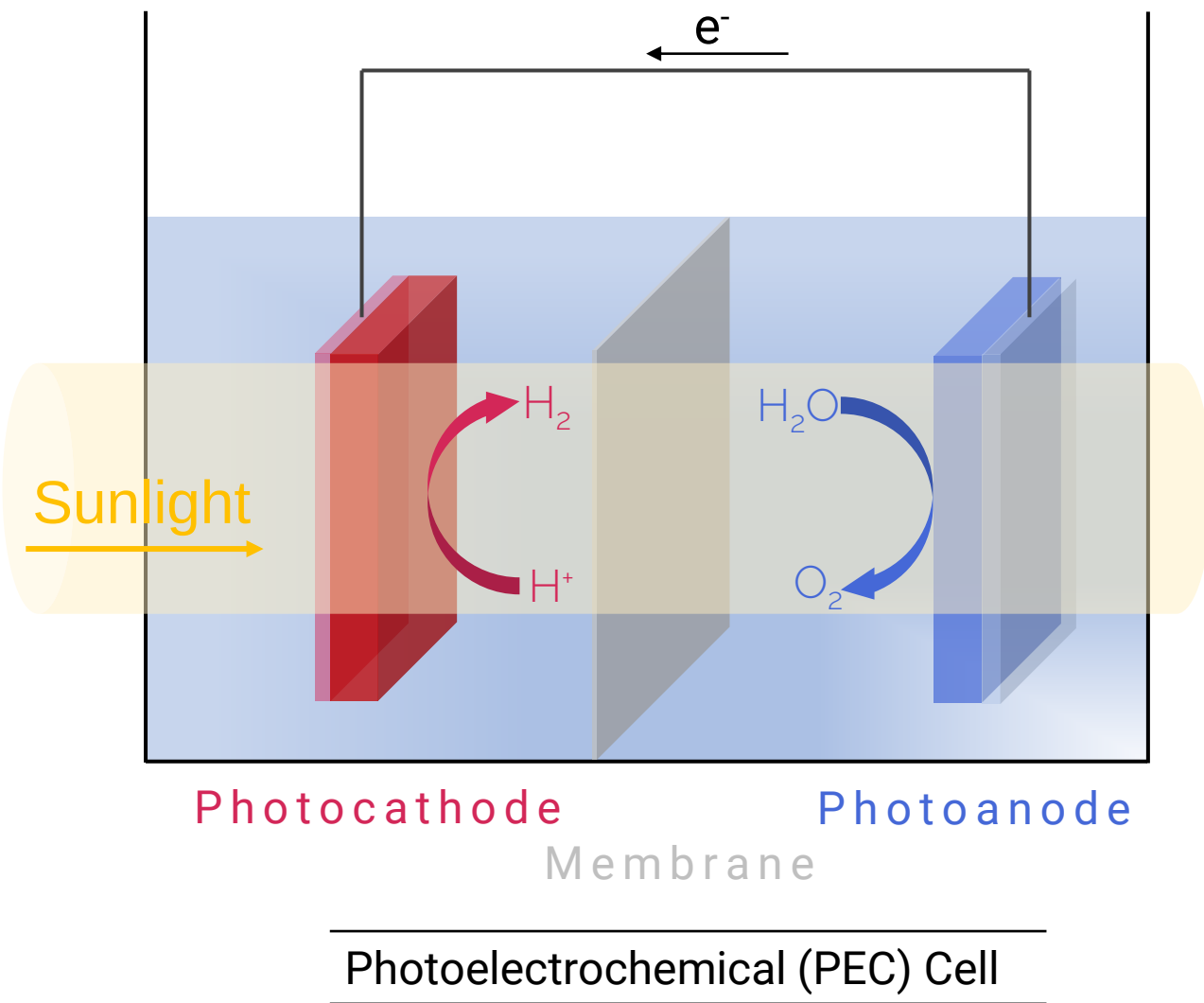
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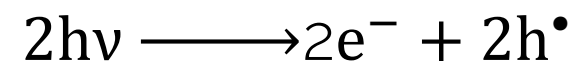


Photoelectrochemical Water Splitting

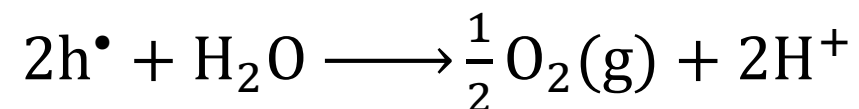


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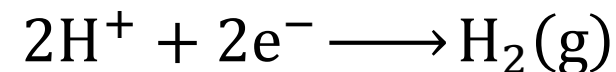
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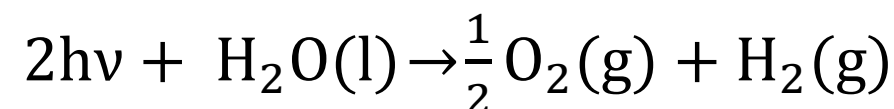
Photoanode: Water Oxidation



Photocathode: Water Reduction



Overall reaction:



Photoelectrode Materials

Material Requirements

Bandgap: $\sim 1.8 - 2.0$ eV

Band Alignment

Adsorption Coefficient

Stable in water

High diffusion length and mobility

Photoelectrode Materials

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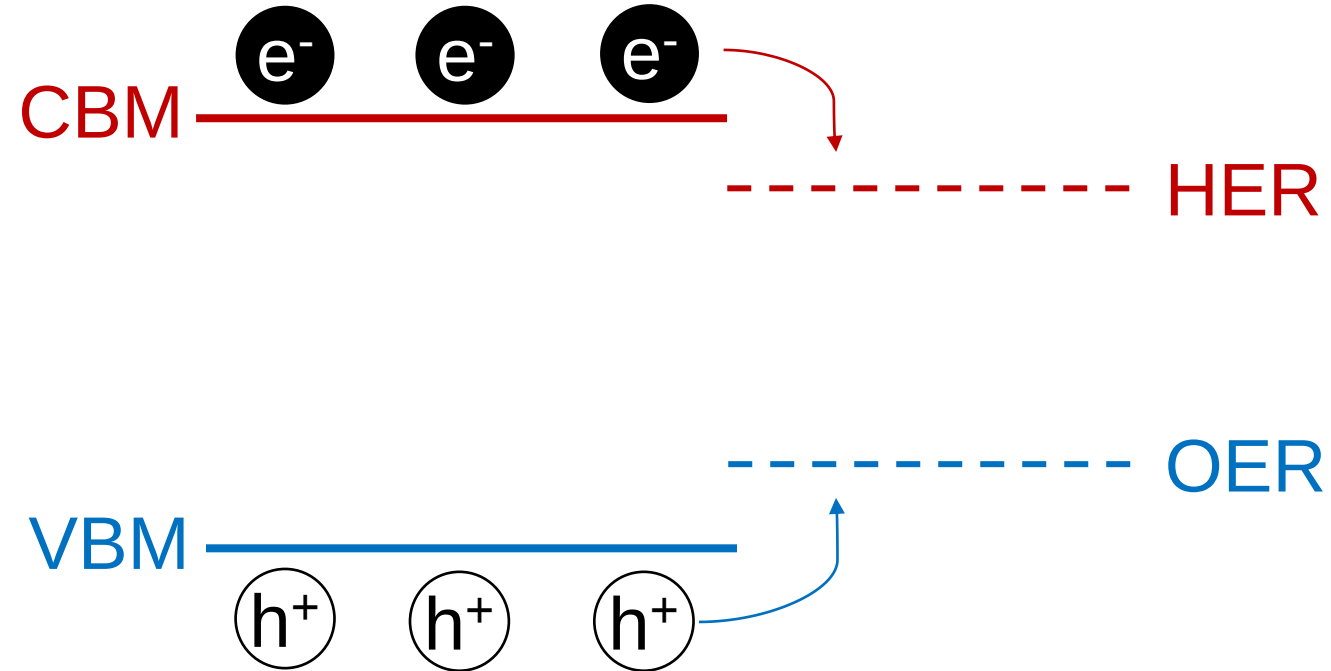
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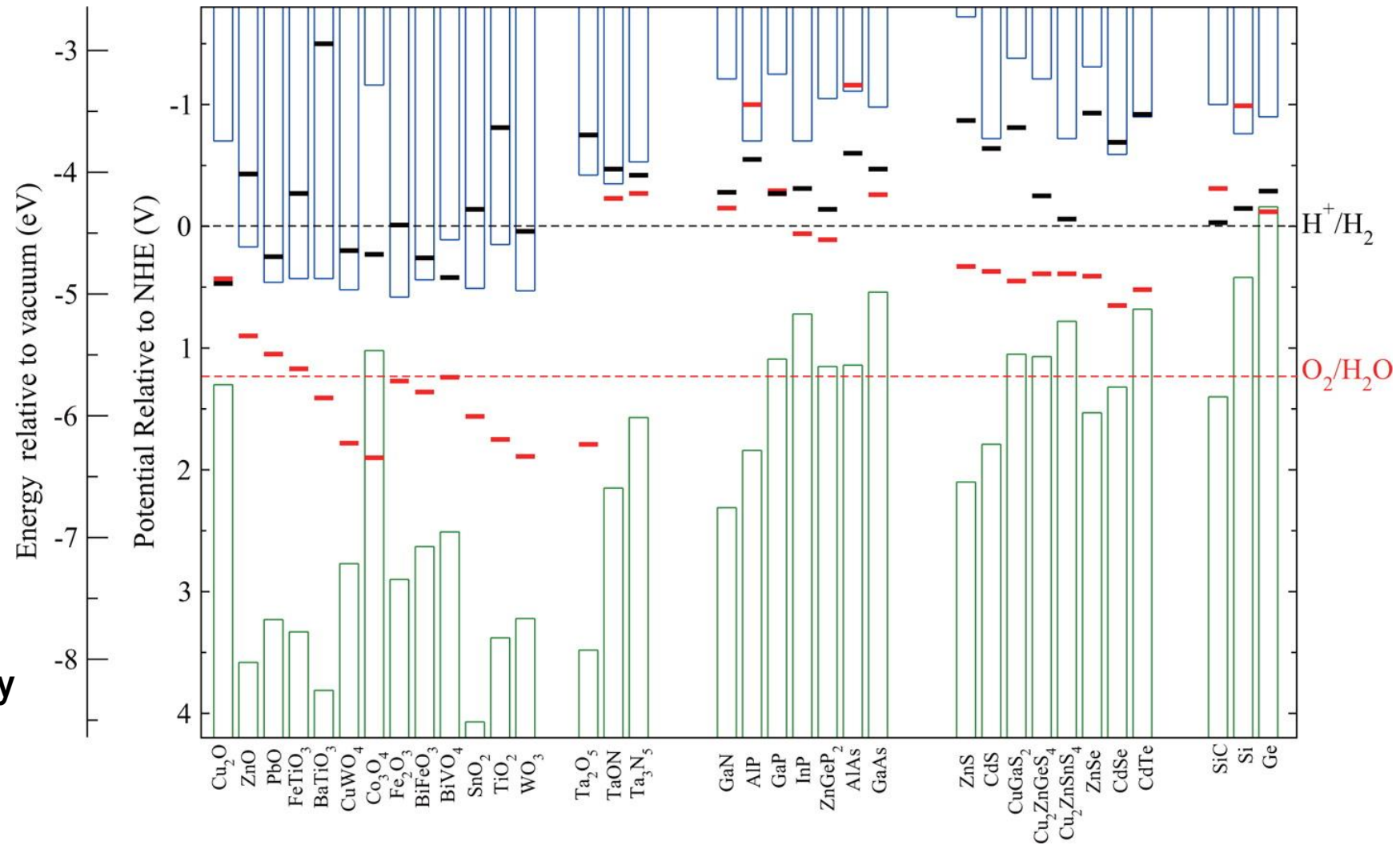
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Chem. Mater. 2012, 24, 18, 3659–3666

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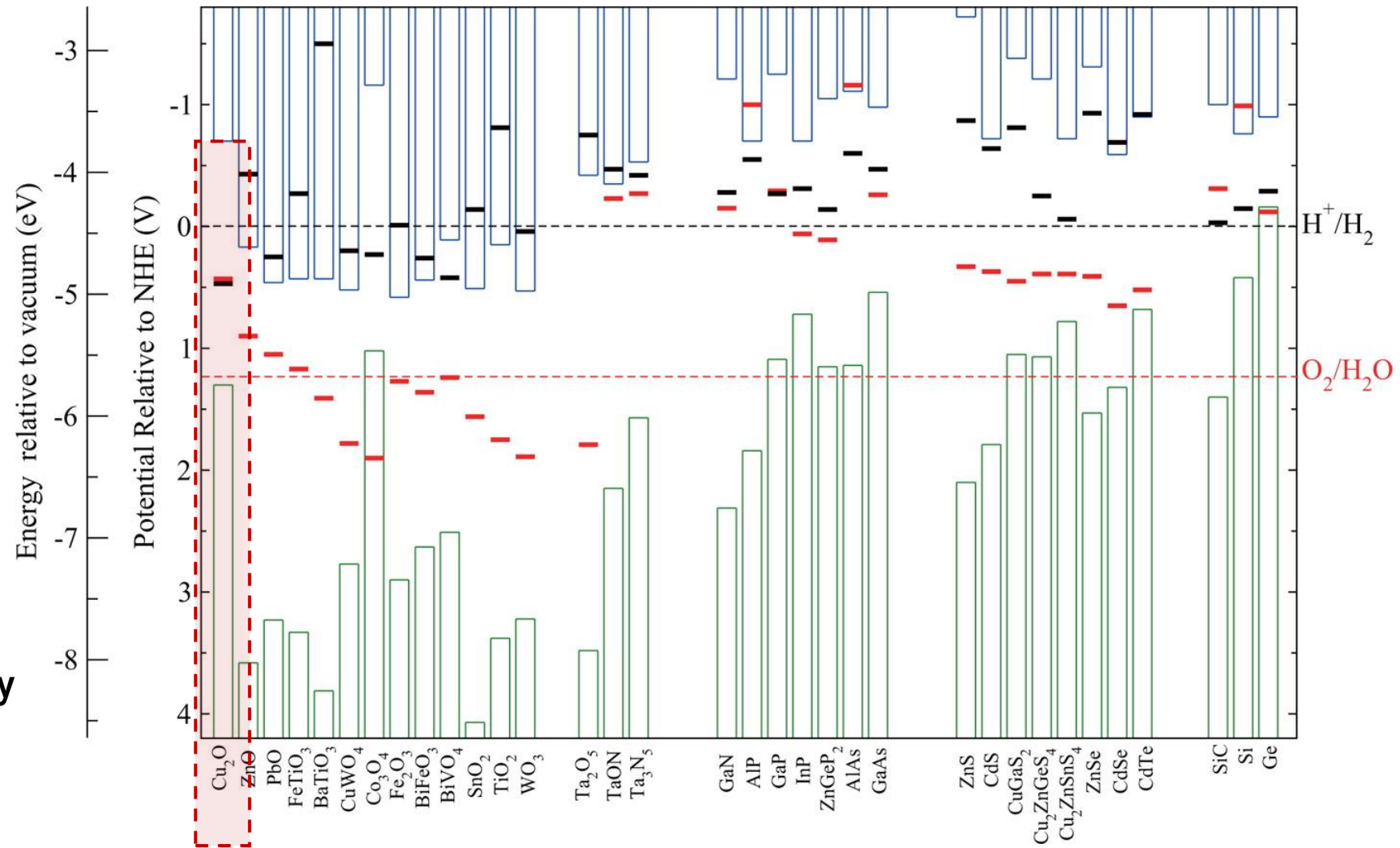
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Cu₂O Photocathode

Cu₂O Photocathode

CBM negative of E_{H^+/H_2}^0 : **Photocathode**

Band gap: **2.0 eV**

Absorption Coefficient: **10⁴ cm⁻¹**

Max. photocurrent: **-14.7 mA-cm⁻²**

Solar to Hydrogen (STH) efficiency: **18 %**

Challenges:

- Photo-corrosion
- Low minority carrier diffusion length

Cu₂O Photocathode

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CBM negative of E_{H^+/H_2}^0 : **Photocathode**

Band gap: **2.0 eV**

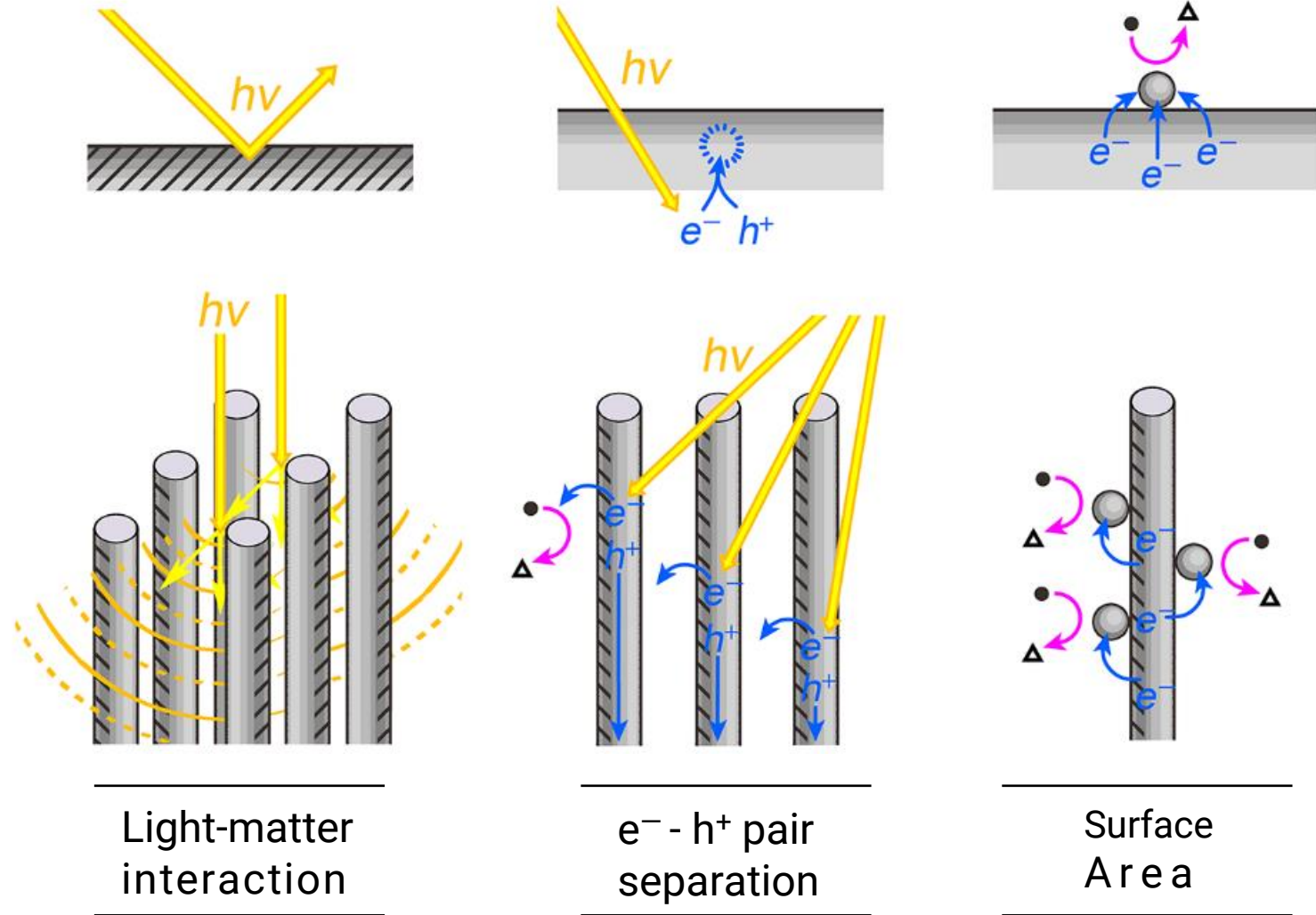
Absorption Coefficient: **10^4 cm^{-1}**

Max. photocurrent: **-14.7 mA-cm^{-2}**

Solar to Hydrogen (STH) efficiency: **18 %**

Challenges:

- Photo-corrosion
- **Low minority carrier diffusion length**



Strategy



Cu_2O Electrodeposition



Nanostructuring

Simple Electrochemical Synthesis

Synthesis of porous Cu_2O

Solution:

0.2 M CuSO_4 + 3M Lactic Acid + 0.1M K_2HPO_4 Buffer

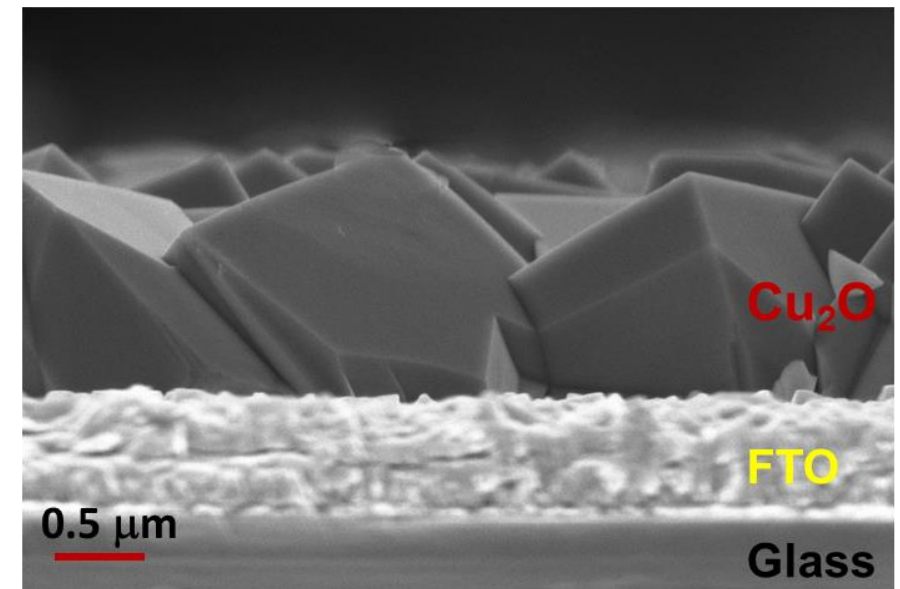
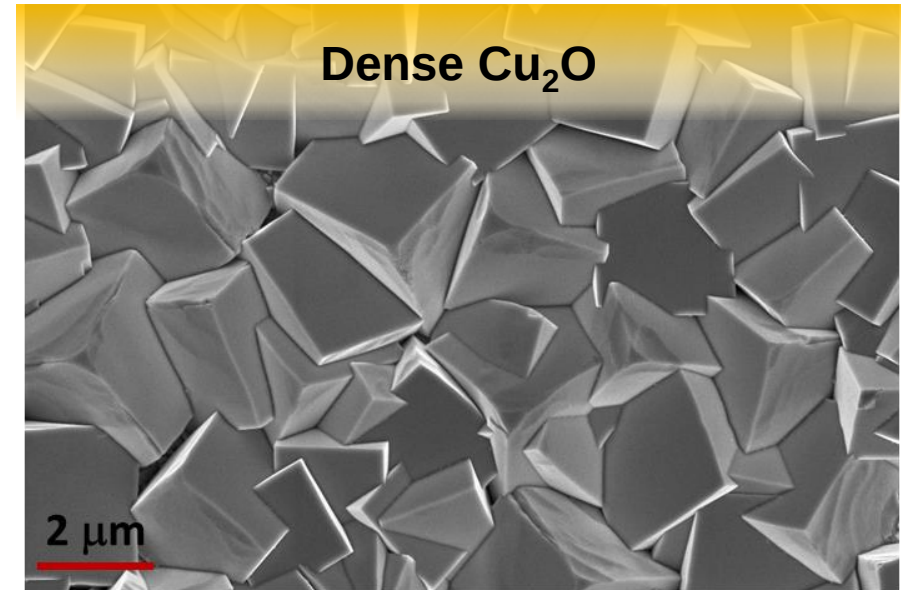
pH: 12 (Maintained by addition of 2M KOH)

Potential: -0.35 V (vs. Ag/AgCl)

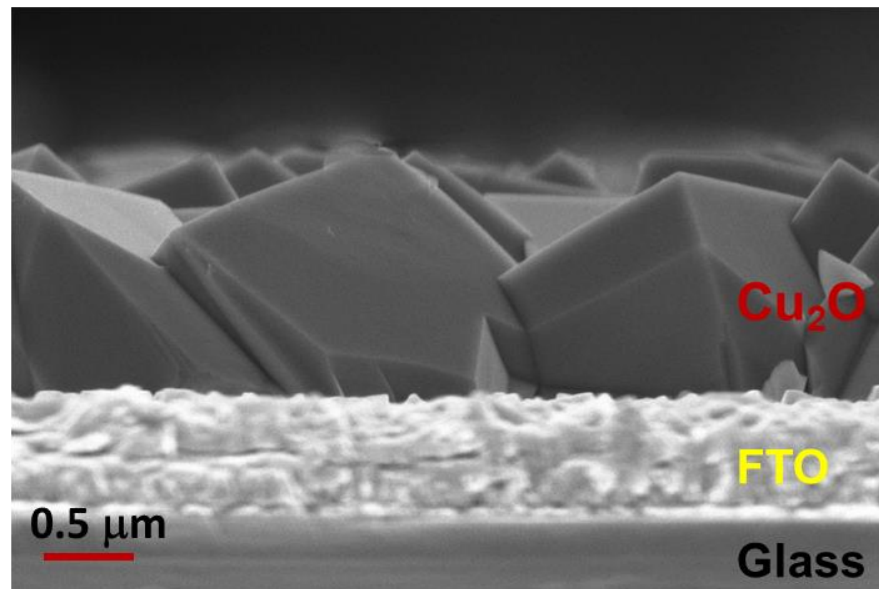
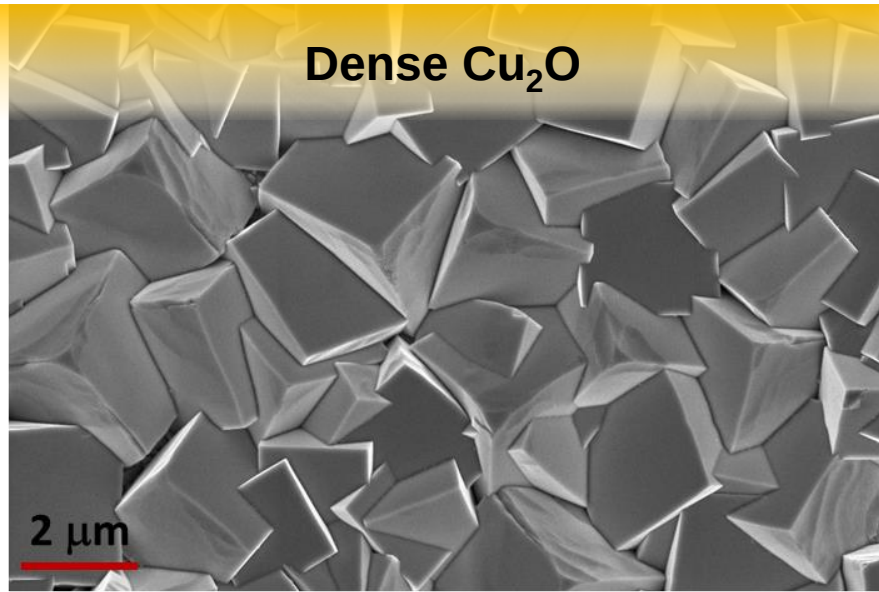
Bath temperature: 55 $^{\circ}\text{C}$

Duration: 15 min

Thickness: 1 μm approx.

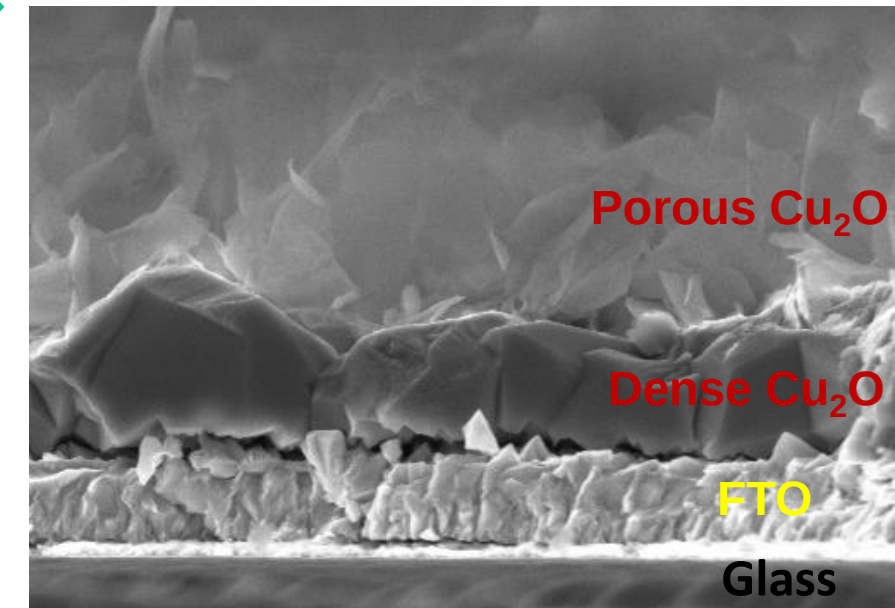
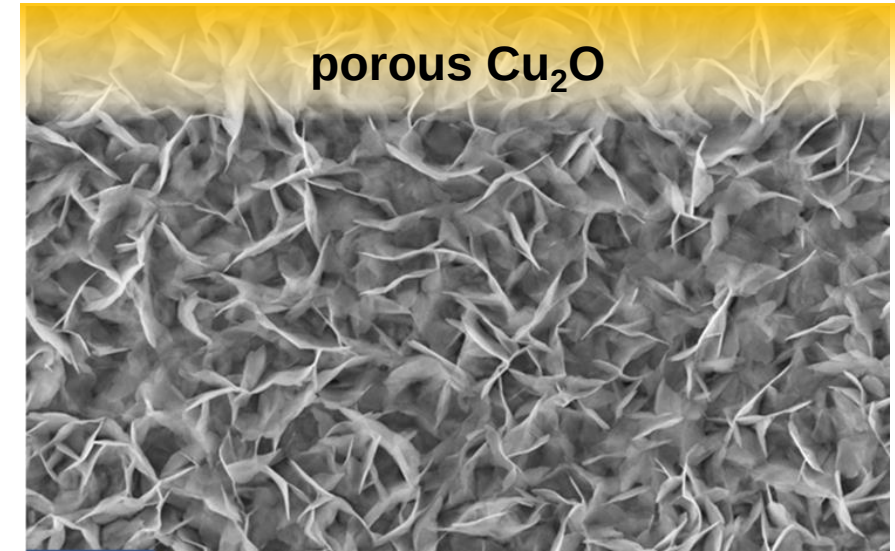
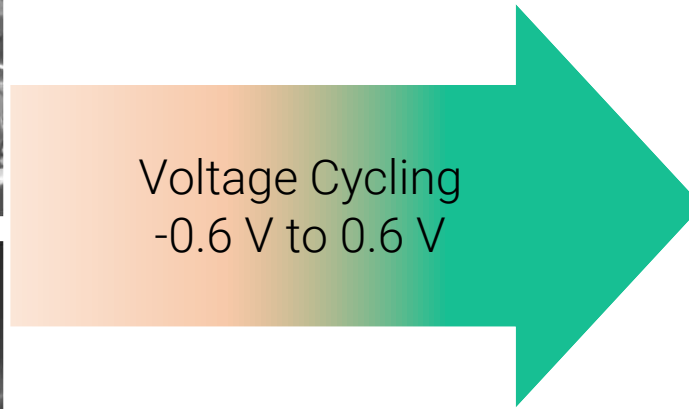
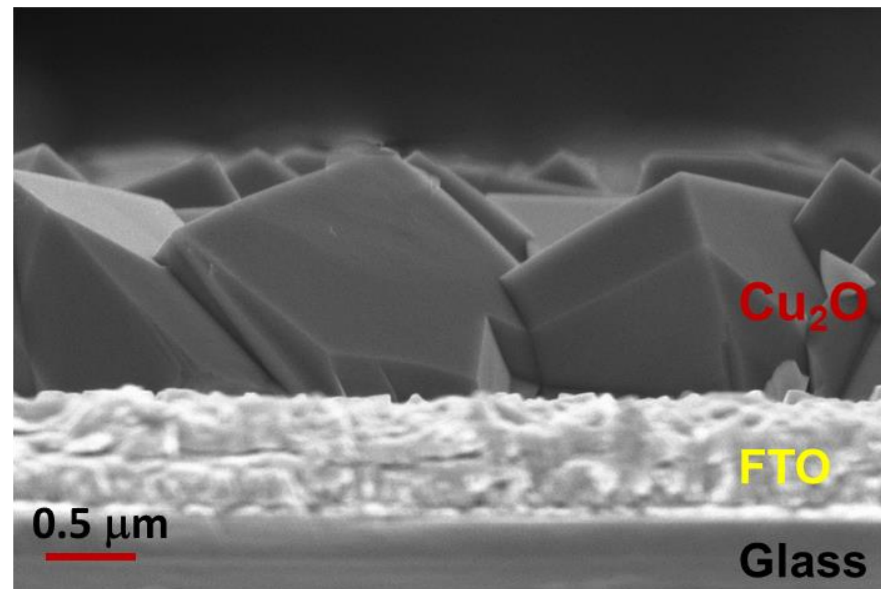
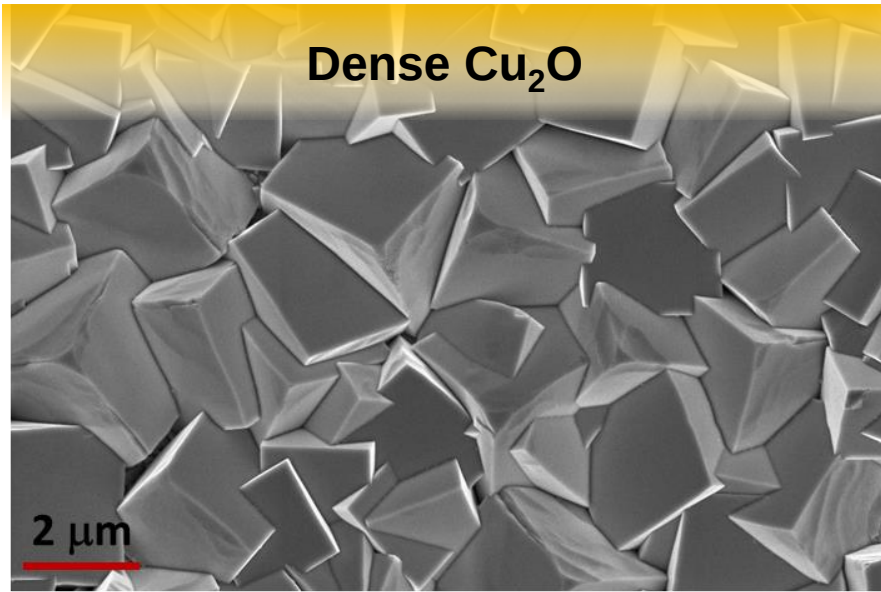


Synthesis of porous Cu_2O

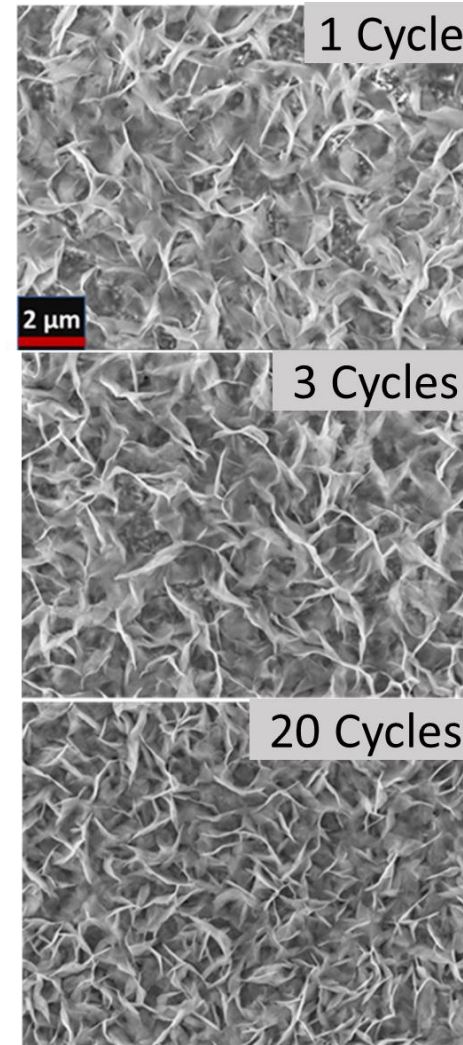
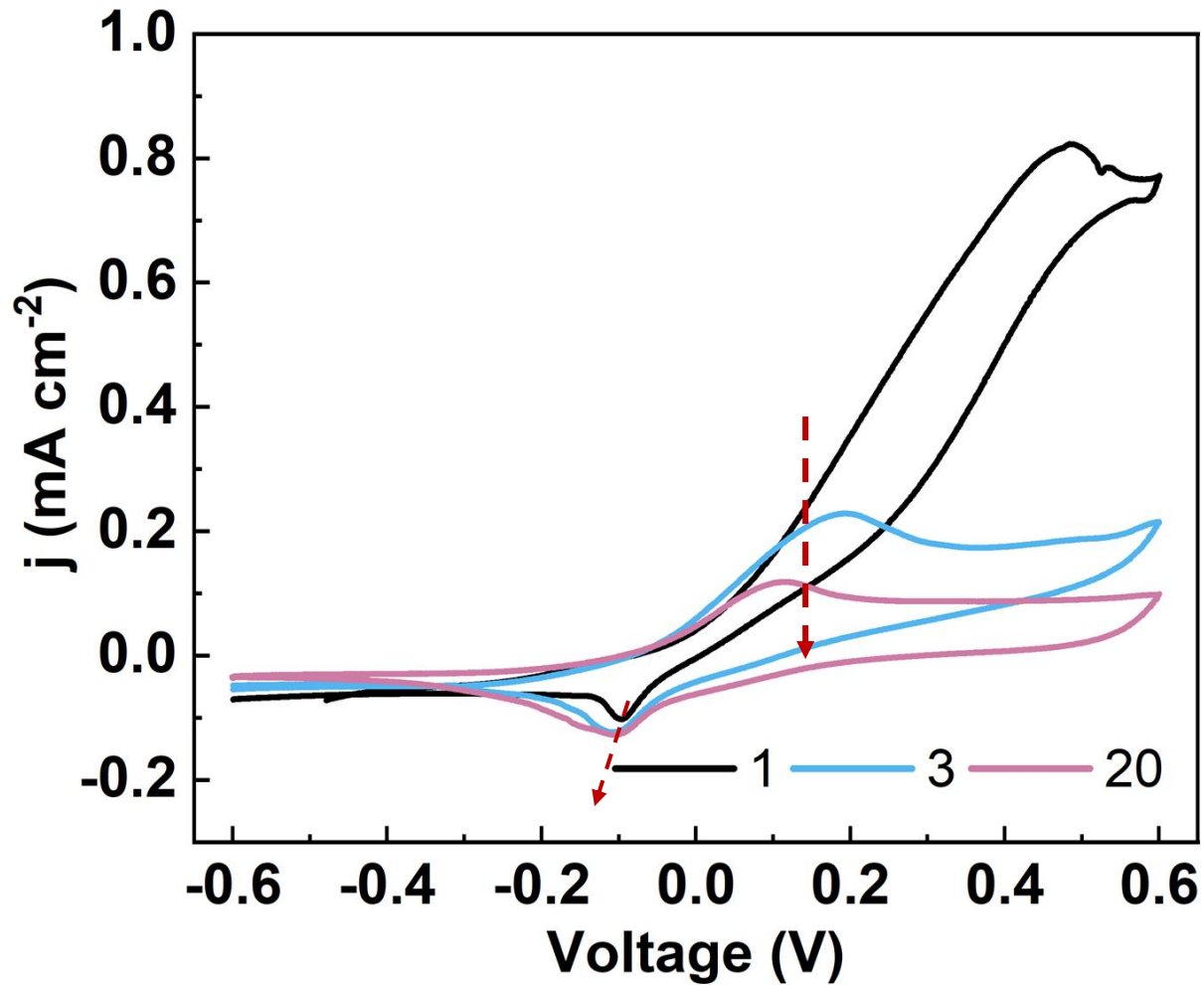


Voltage Cycling
-0.6 V to 0.6 V

Synthesis of porous Cu_2O

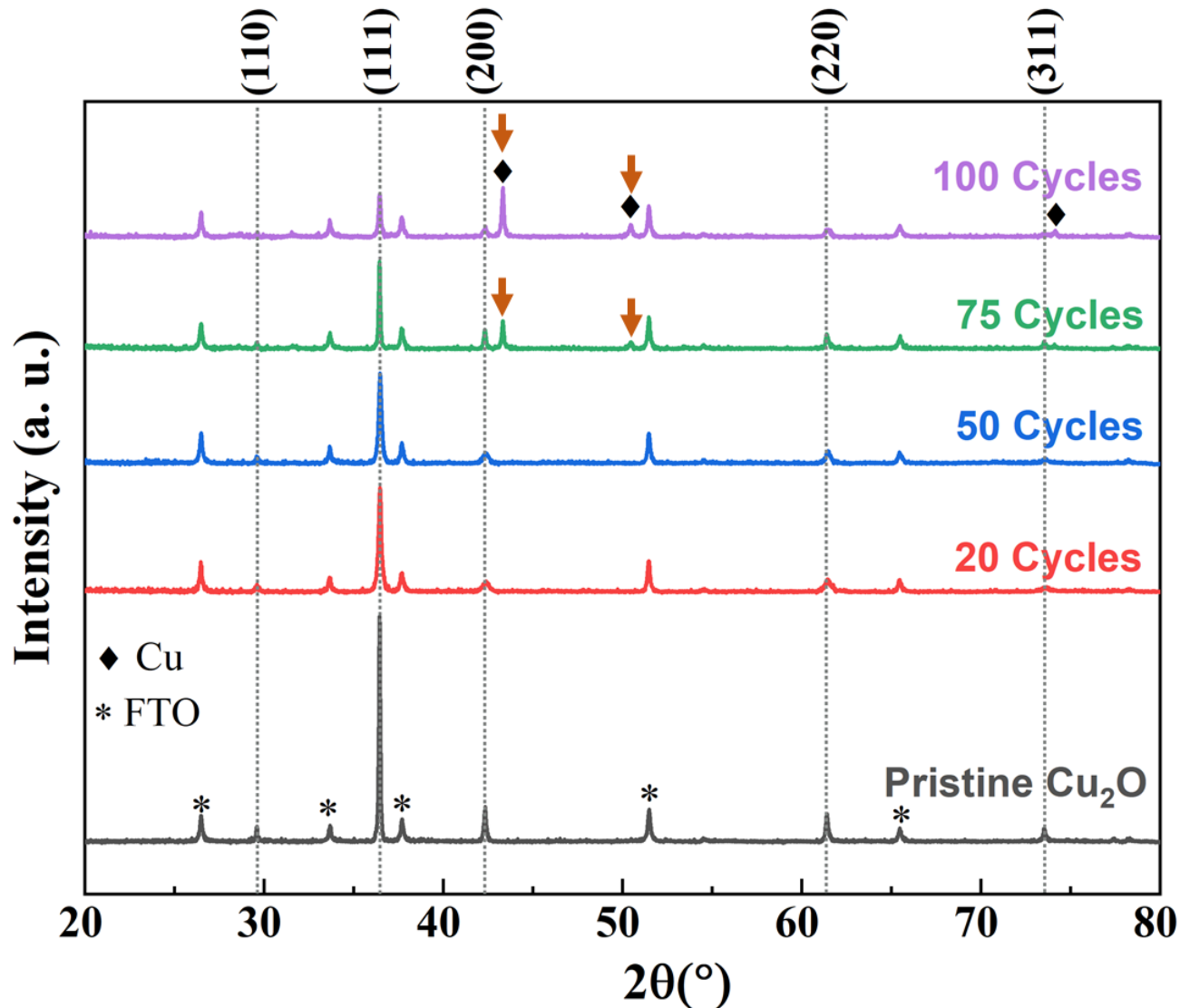


Morphology Evolution



- Porous morphology forms within first cycle
- After 5 cycles complete coverage

Etching and Formation of Cu-impurity



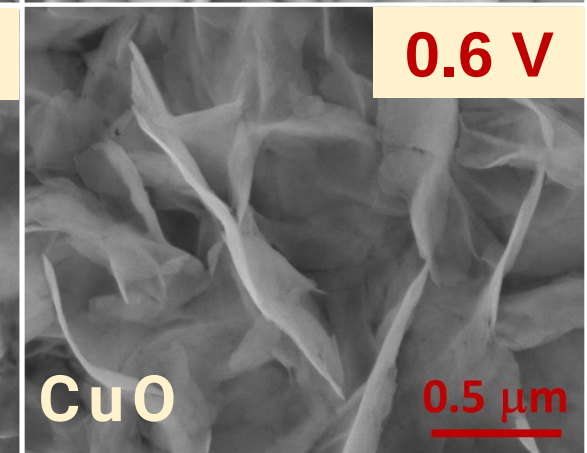
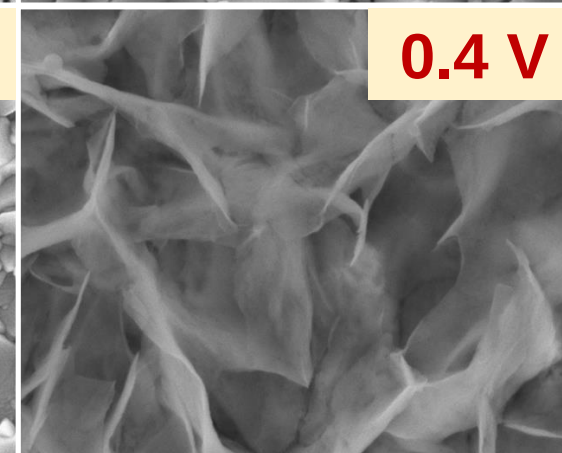
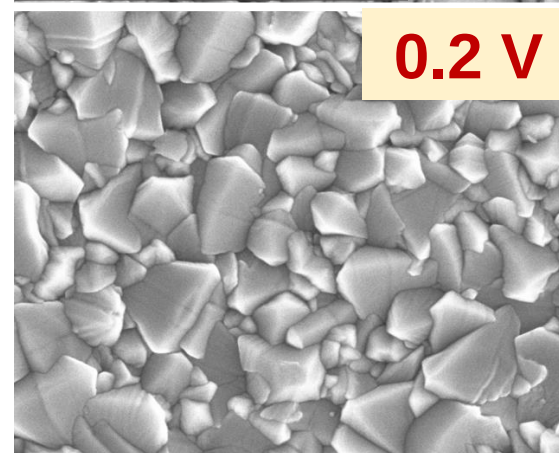
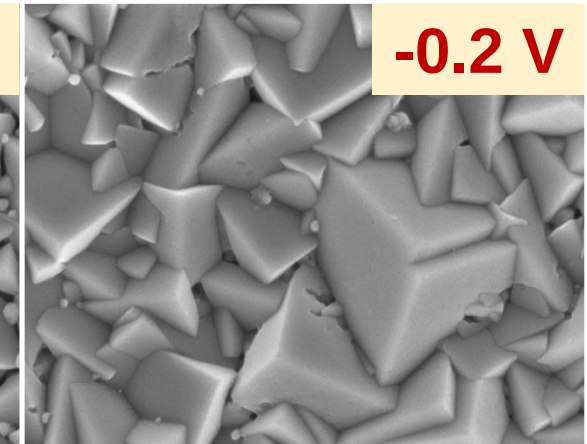
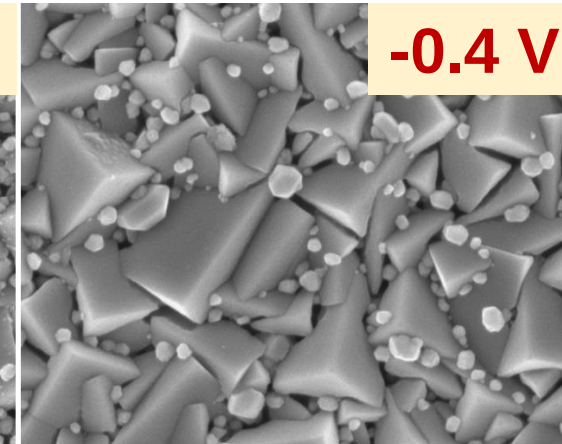
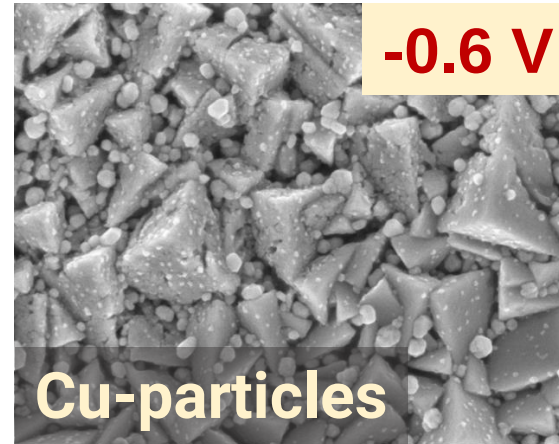
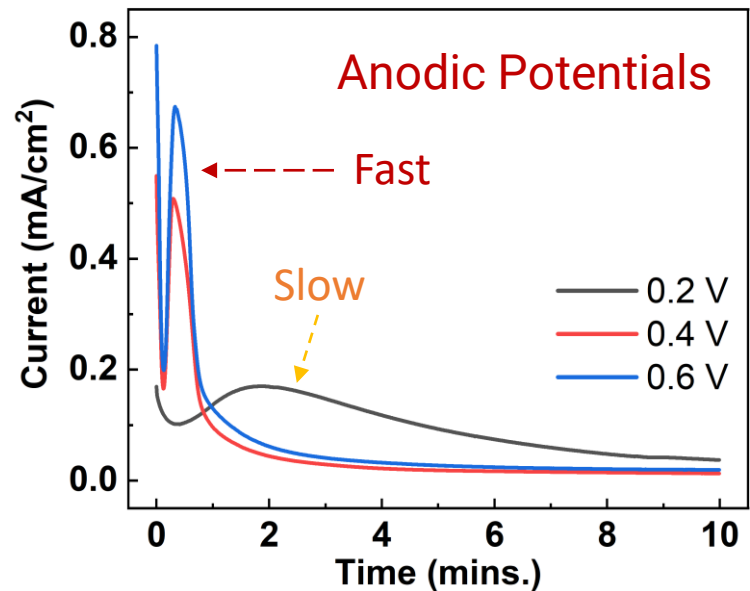
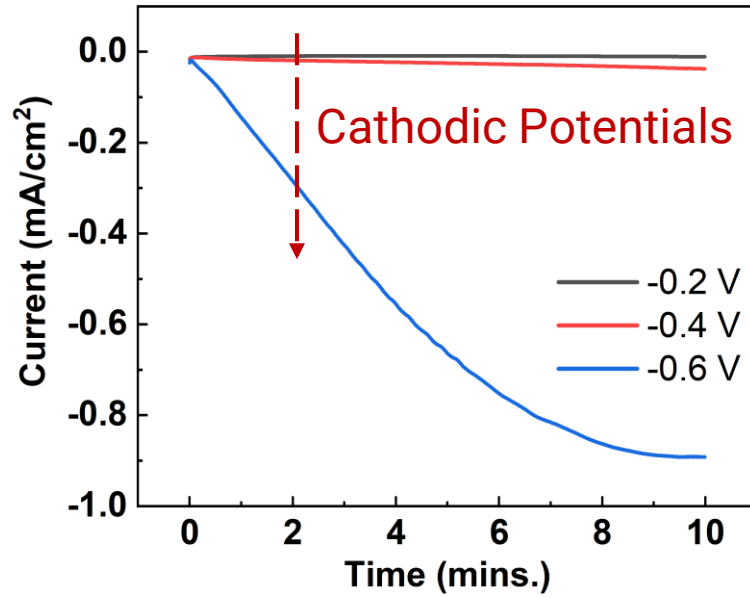
Reduction in Cu₂O peaks: Indication of **etching**

	Cu ₂ O (111)	FTO (110)	Ratio
Pristine Cu ₂ O/FTO	3482	540	6.45
Porous (20 cycle)	2800	522	5.36

Presence of **Cu impurity** after 50 cycles:

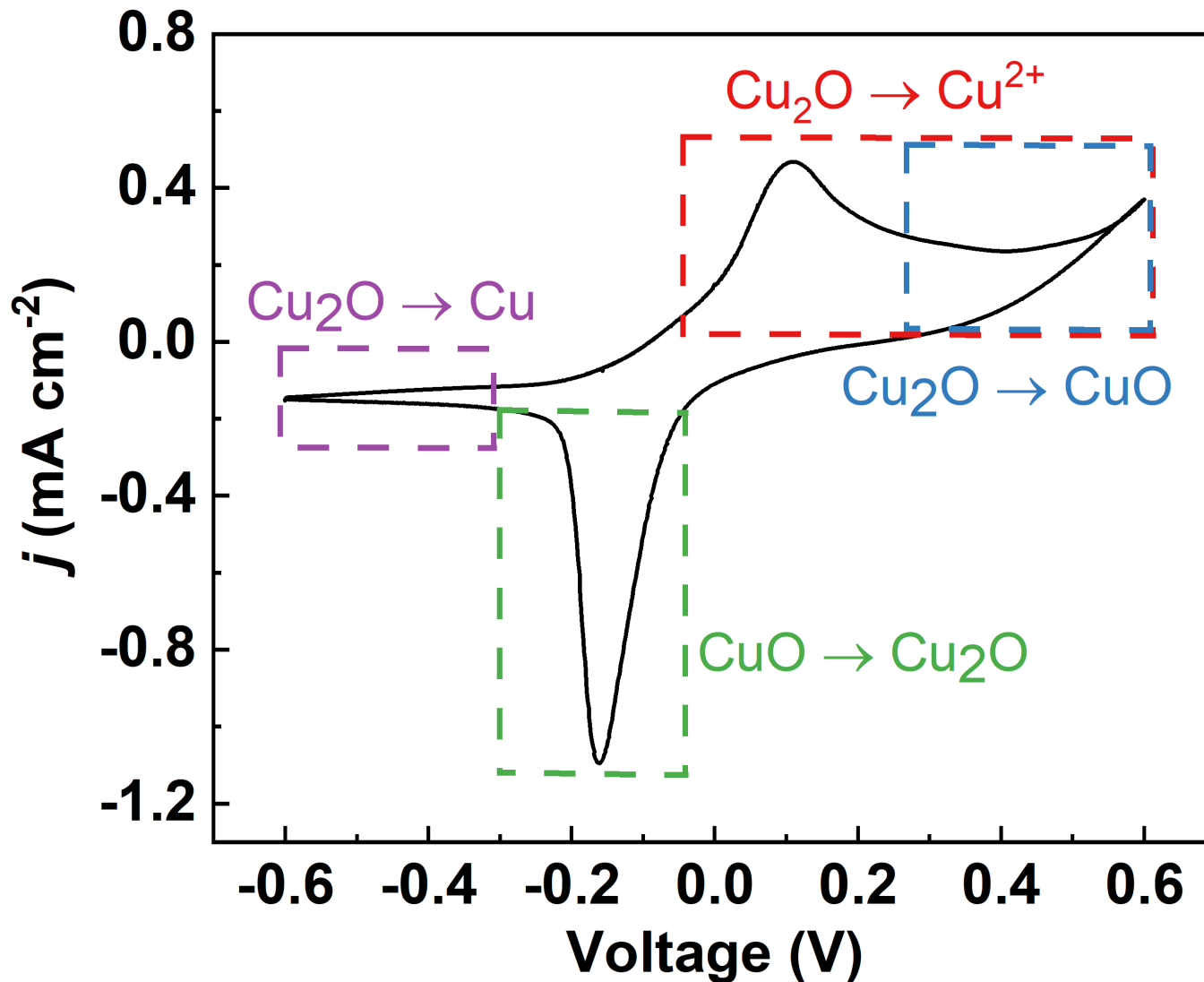
Slow reduction kinetics

Potentiostatic hold



- Etching is observed during Potentiostatic hold at 0.2 V
- Cu₂O oxidized to either CuO or Cu(OH)₂
- Formation of a porous blocking layer at higher anodic potentials

Formation mechanism of porous Cu₂O



0.0 V to 0.6 V: XRD & ICP-AES



0.3 V to 0.6 V: CuO LSV & Pot. hold



0.0 to -0.3 V: LSV analysis of CuO & Cu₂O

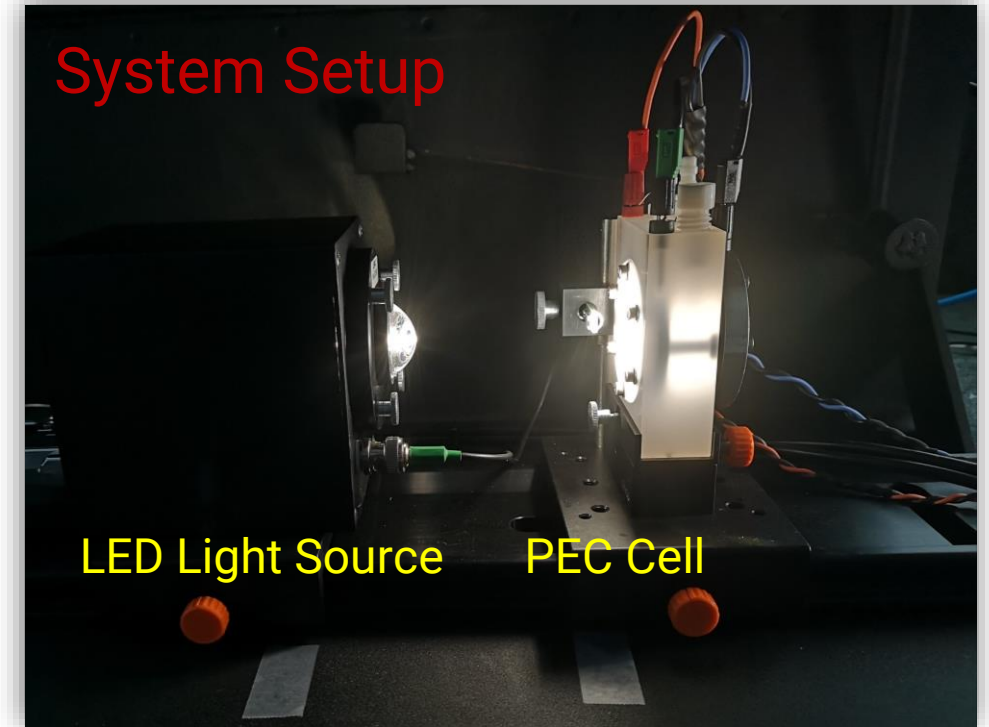
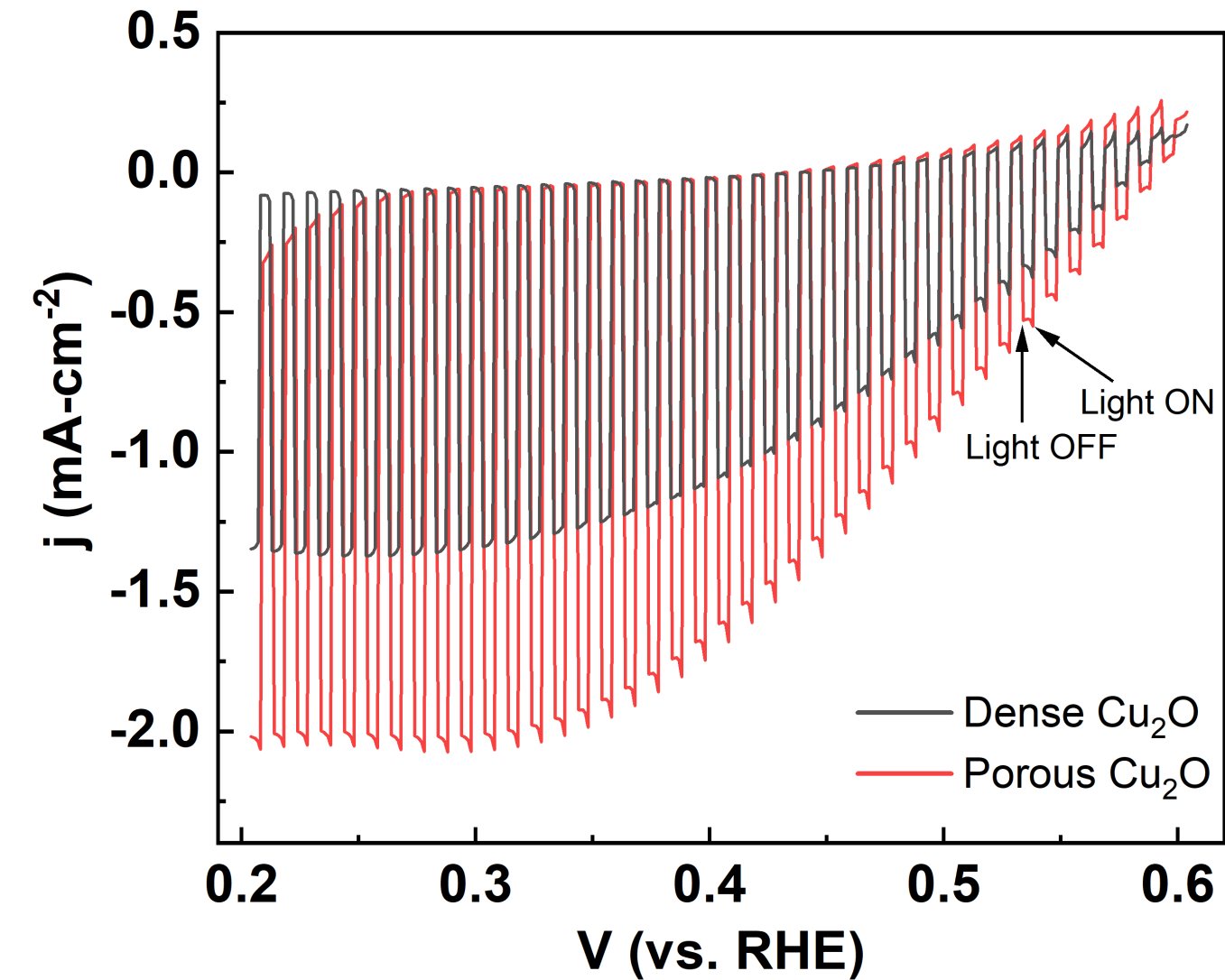


-0.3 V to -0.6 V: Pot. Hold

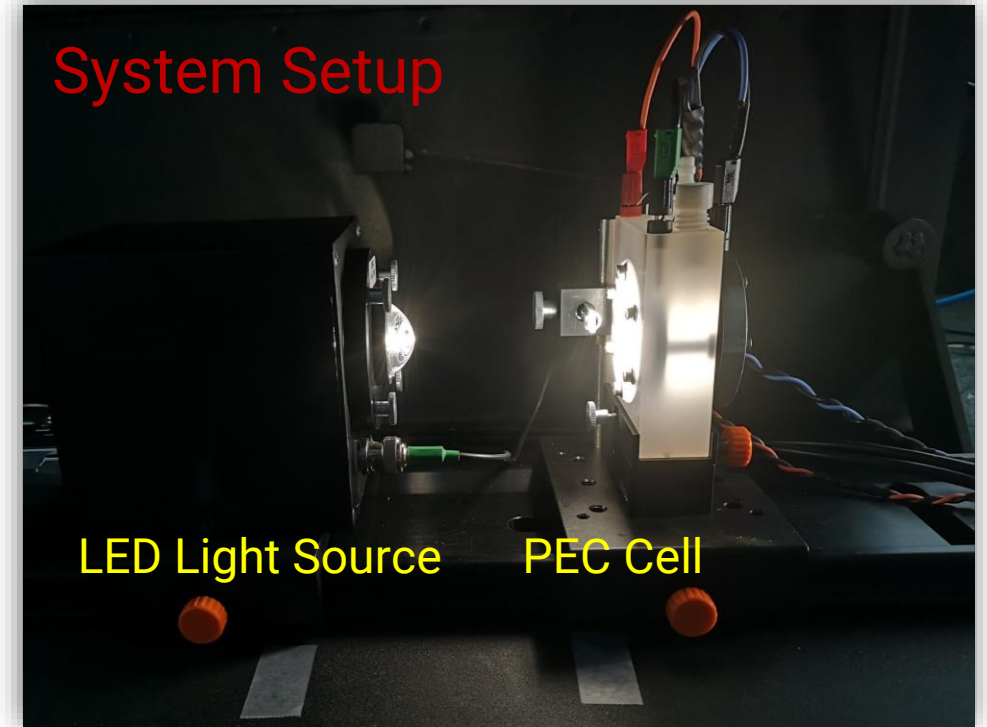
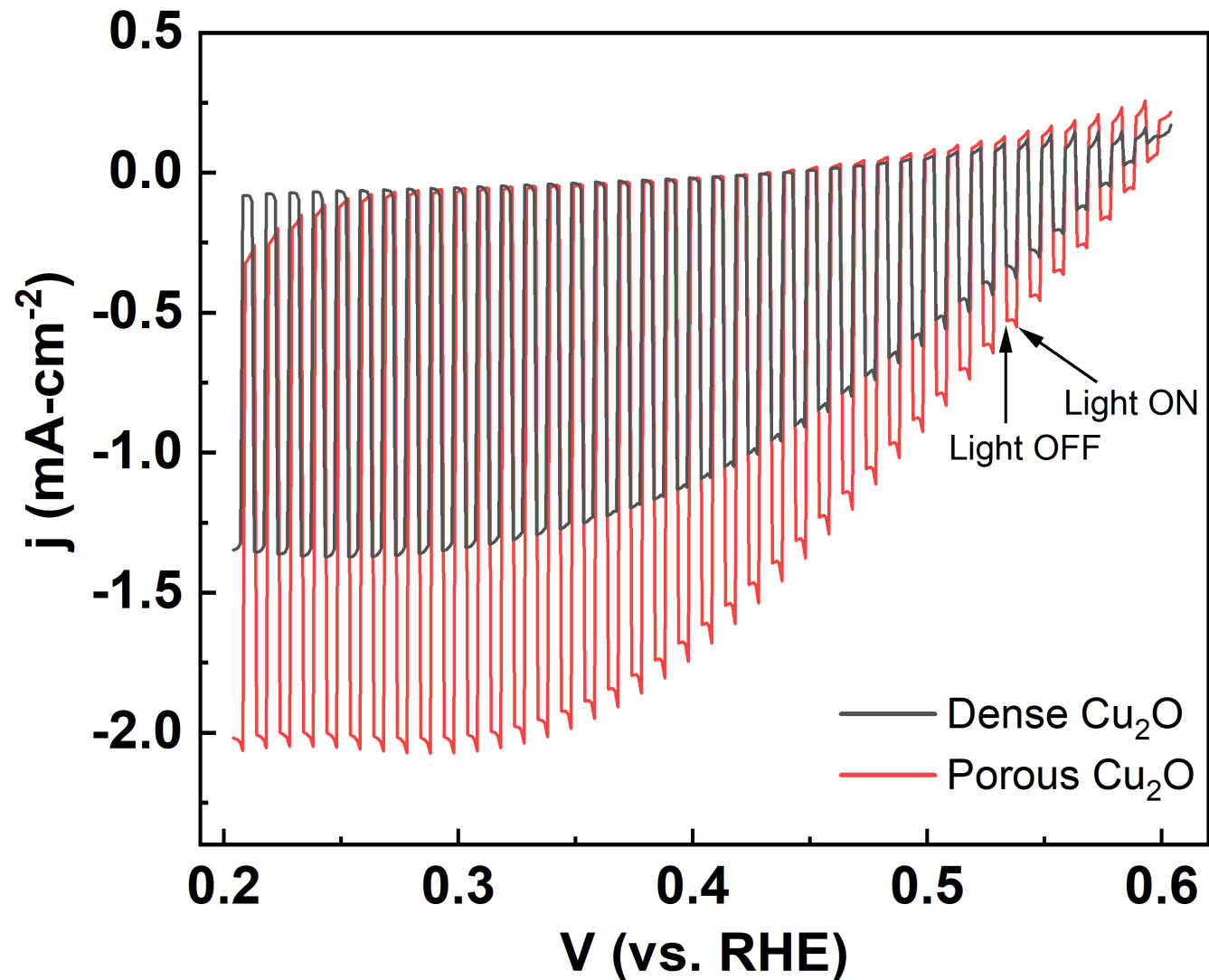


- Etching
- Cu₂O oxidation to CuO
- CuO reduction to Cu₂O
- Cu₂O reduction to Cu

PEC Performance



PEC Performance



Photocurrent enhancement due to:

- Better light trapping
- Orthogonal charge separation
- Increased electrode-electrolyte contact area

Conclusions

- Two step **electrochemical synthesis** of nanostructured Cu_2O thin films
- Nanostructured thin films show a **photocurrent enhancement of 50%** compared to dense film

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Publication:

Akhilender Jeet Singh, Garima Aggarwal, Chandan Das, K.R. Balasubramanian, *Journal of The Electrochemical Society*, 168, 032504, 2021

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Lab-mates & Friends

Chandan Das

Garima Aggrawal

Suren Patwardhan

Sushobhita Chawala

Gurudayal Behera

Faleela

Thank You !!

Questions ??

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